Stitch Aware Detailed Placement for Multiple E-Beam Lithography

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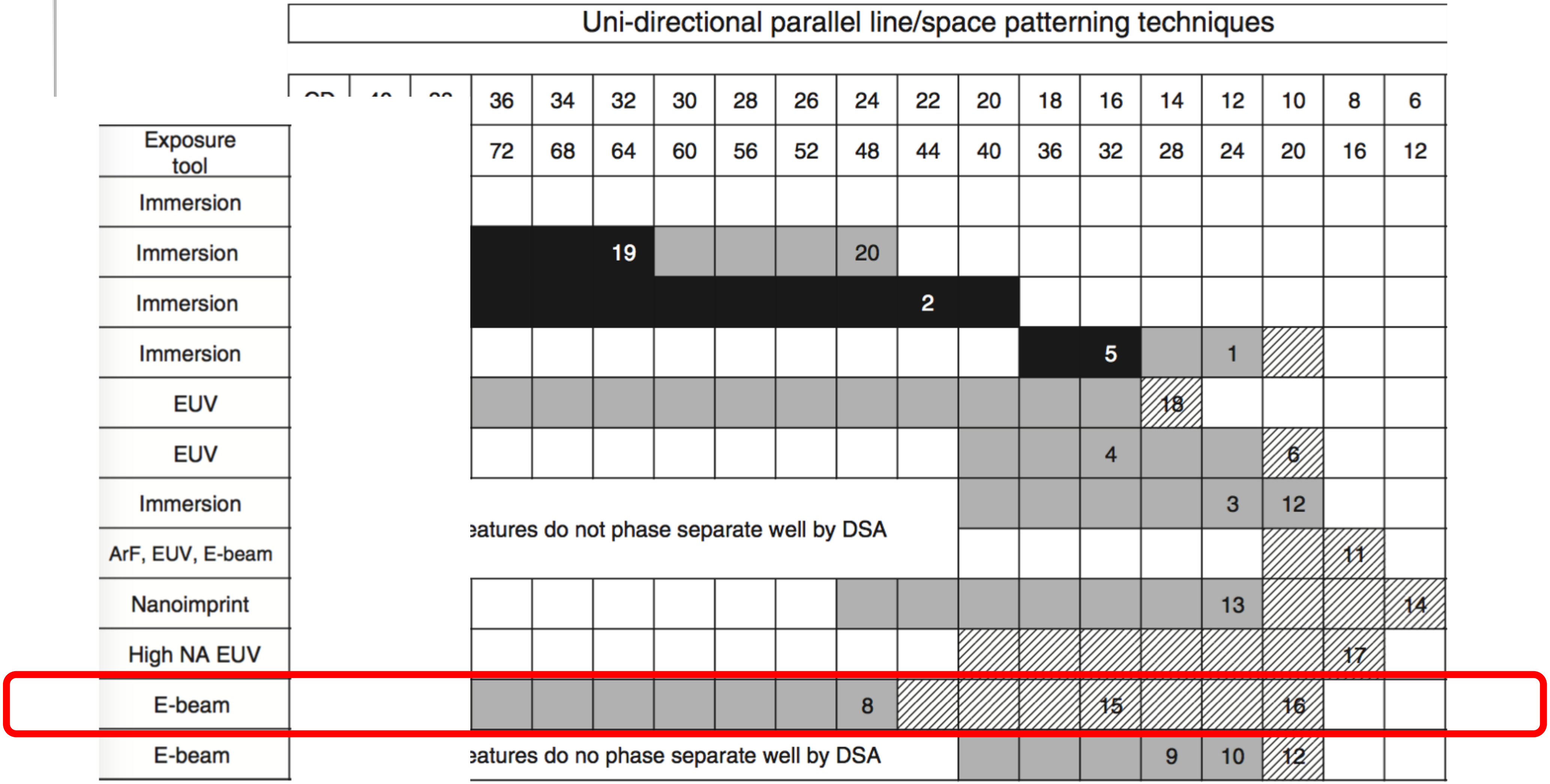
Outline

- Introduction
- Previous Work
- Problem Formulation
- Stitch Aware Detailed Placement
- Experimental Results
- Conclusion

Introduction

- Technology Scaling



Uni-directional parallel line/space patterning techniques

	CD	40	38	36	34	32	30	28	26	24	22	20	18	16	14	12	10	8	6
Exposure tool				72	68	64	60	56	52	48	44	40	36	32	28	24	20	16	12
Immersion																			
Immersion				■	■	■ 19	▒	▒	▒	▒ 20									
Immersion				■	■	■	■	■	■	■	■ 2	■							
Immersion													■	■ 5	▒	▒ 1	▨		
EUV				▒	▒	▒	▒	▒	▒	▒	▒	▒	▒	▒	▨ 18				
EUV												▒	▒	▒ 4	▒	▒	▨ 6		
Immersion				eatures do not phase separate well by DSA								▒	▒	▒	▒	▒ 3	▒ 12		
ArF, EUV, E-beam																	▨	▨ 11	
Nanoimprint										▒	▒	▒	▒	▒	▒	▒ 13	▨	▨	▨ 14
High NA EUV												▨	▨	▨	▨	▨	▨	▨ 17	
E-beam				▒	▒	▒	▒	▒	▒	▒ 8	▨	▨	▨	▨ 15	▨	▨	▨ 16		
E-beam				eatures do no phase separate well by DSA								▒	▒	▒	▒ 9	▒ 10	▨ 12		

[Courtesy ITRS]

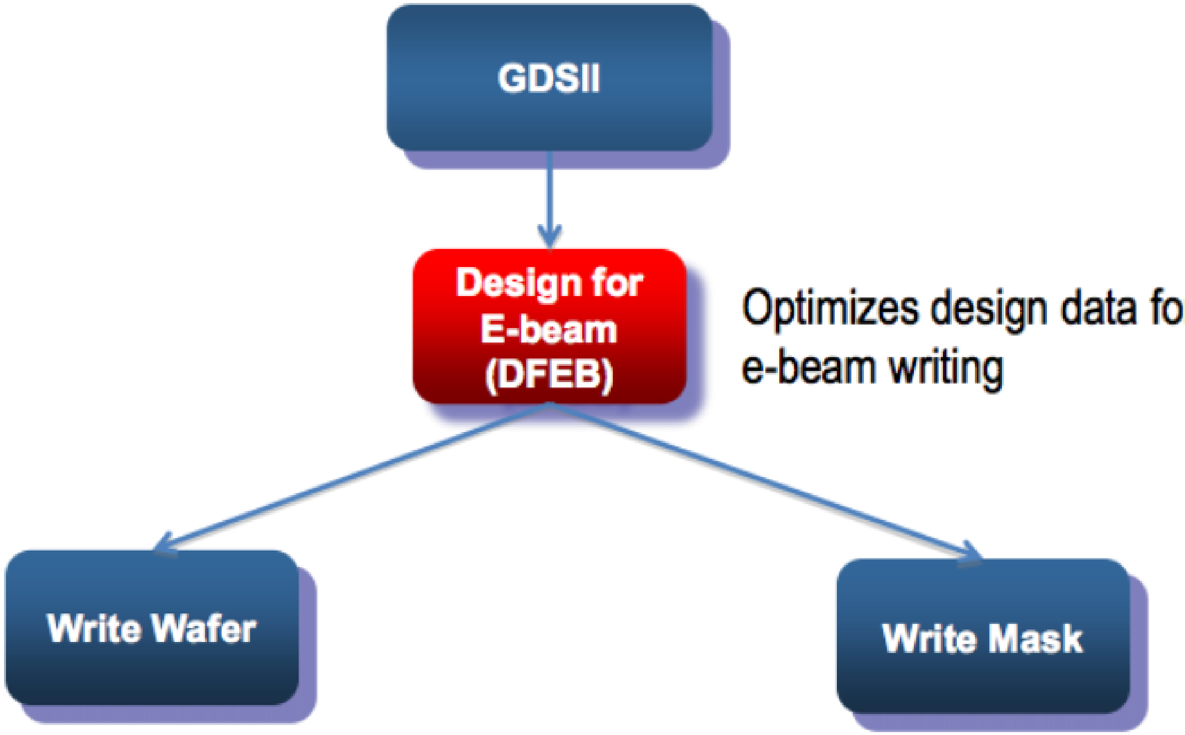
■ Consenses that technique has been used in production

▒ Published demonstrations from potential deployable equipment show opportunity for production

▨ Simulations, surface images, or research grade demonstration suggest potential for extendability

E-Beam Lithography

- Direct-write or mask?



Optimizes design data for e-beam writing

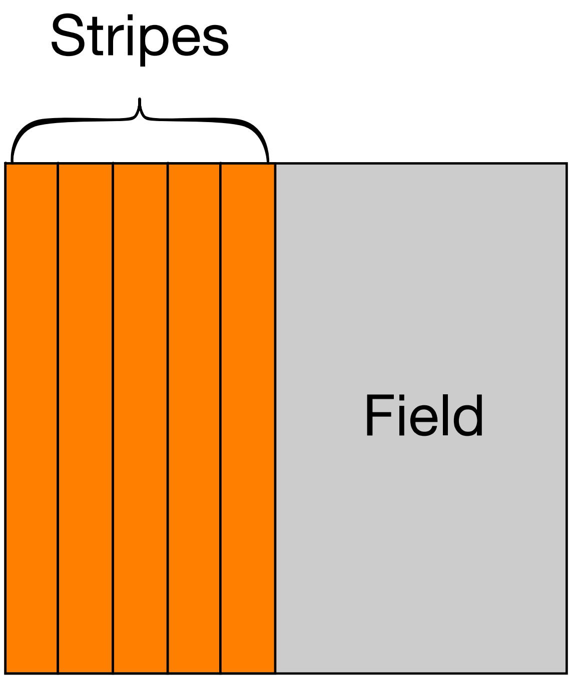
Contacts/Cuts First
Enables Lower Volume at Leading Nodes

Any Volume
Any Layer

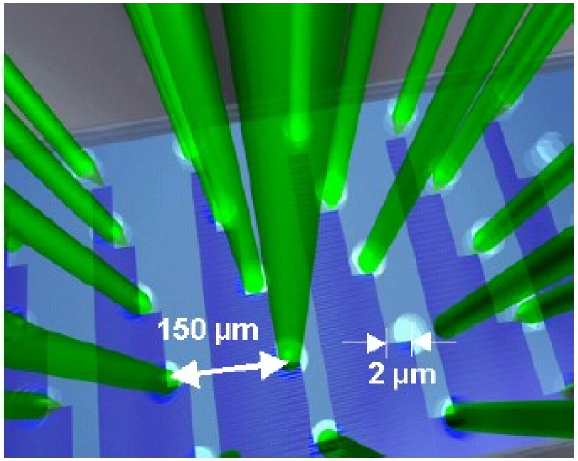
[Courtesy E-beam Initiative]

Multiple E-Beam Lithography

- Massively-Parallel e-beam writing
  - Each stripe has width of 50~200 microns
  - Stitching region has a width around 15nm [Berg+,SPIE'11]
  - Field stitching



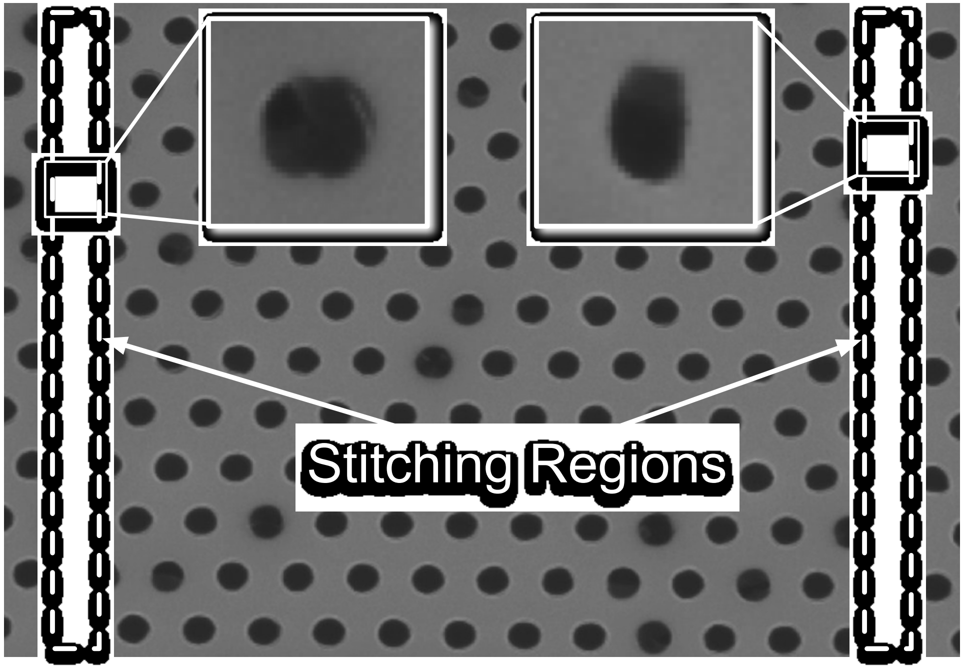
[Fang+,DAC'13]



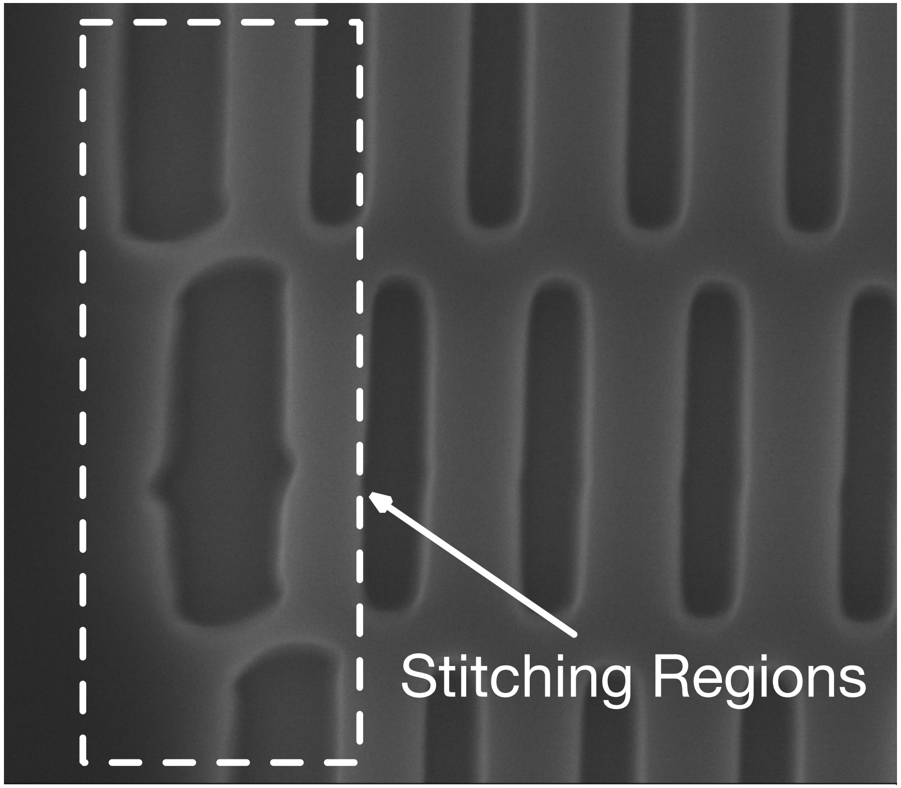
MAPPER Lithography System

Field Stitching

- SEM figures showing stitches at boundaries of beam stripes



Holes



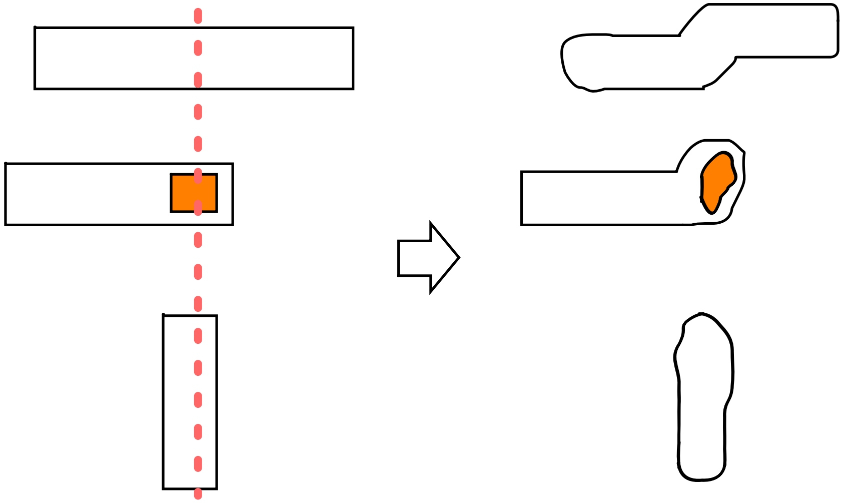
Lines

Previous Work

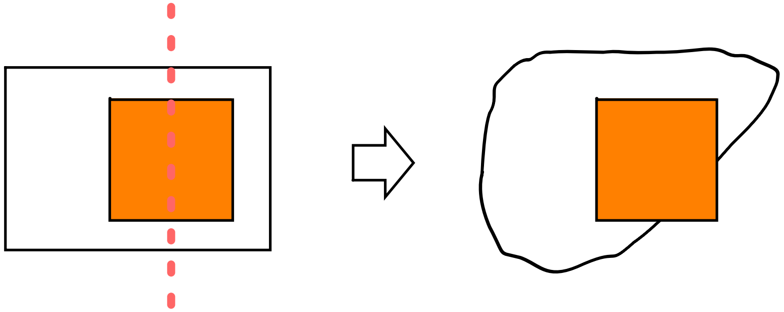
- Stitch aware routing for MEBL
  - [Fang+,DAC’13], [Liu+,TCAD’15]
- TPL aware placement
  - [Yu+,TCAD’15], [Kuang+,TVLSI’15], [Chien+,TCAD’15]
  - [Tian+,ICCAD’14], [Lin+,ISPD’15]
  - TPL applies different constraint to placement from MEBL
- No placement algorithm addressing MEBL stitch constraint yet

Stitch Errors

- Defects on vias and vertical wires

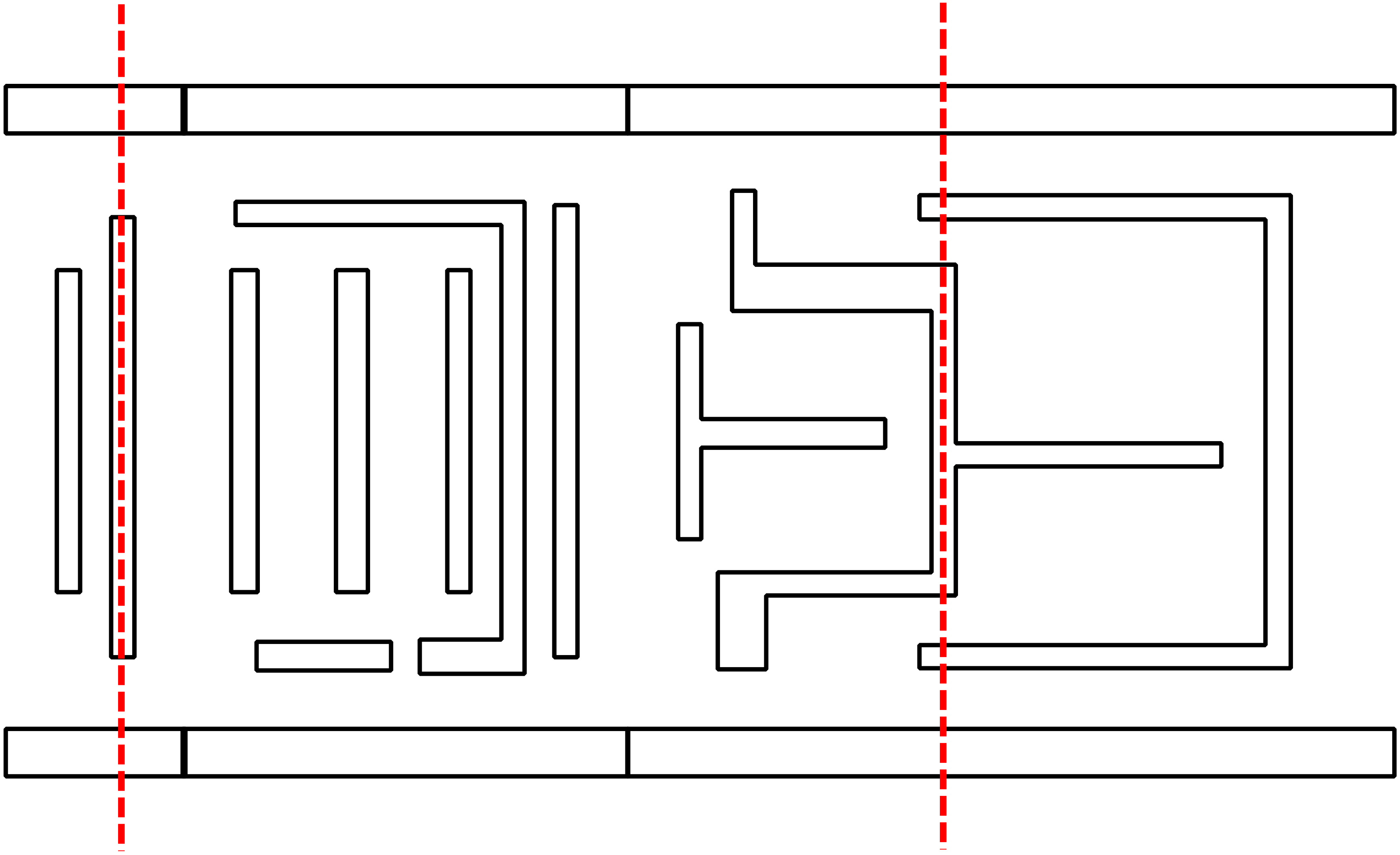


- Defects on short polygons



[Fang+,DAC2013]

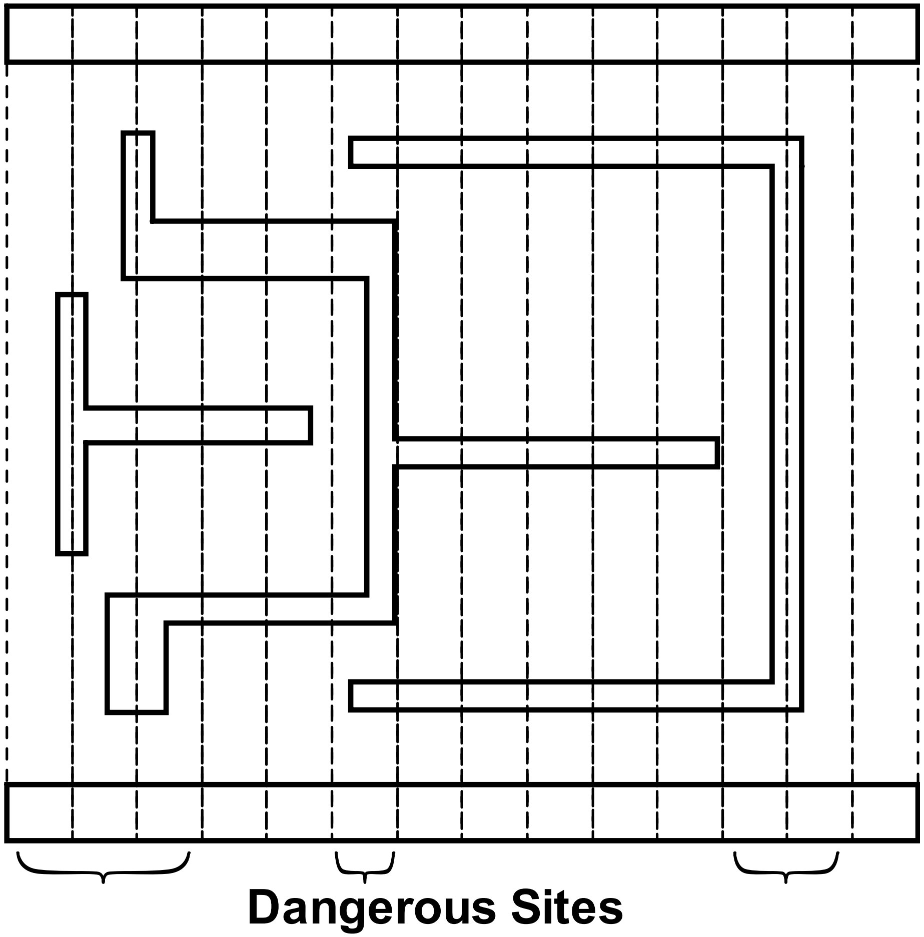
Stitch Errors within Standard Cell



Resolve stitch errors by proper placement

Dangerous Site Representation

- A cell is divided into sites (poly pitch)
- Sites that contain susceptible segments are marked as "dangerous sites"



Problem Formulation

- Input
  - Initial placement
  - Dangerous site information for each standard cell (precomputed)
- Output
  - New placement with optimized wirelength and minimum stitch errors
  - MEBL friendliness

Single Row Placement & Previous Work

- Given a set of ordered cells c_1, c_2, …, c_n, place cells horizontally to minimize objectives such as wirelength or movement
- Previous work on single row algorithm
  - Conventional objectives
    - [Brenner+,DATE'00], [Kahng+,GLSVLSI'04], Abacus [Spindler+,ISPD'08], [Taghavi+,ICCAD'10]
  - TPL awareness
    - [Yu+,ICCAD'13]: O(mnK)
    - [Kuang+,ICCAD'14]

Note: $\tau = 10, \phi = 1, \upsilon = 1$ in the experiment

Single Row Placement

- Given a set of ordered cells c_1, c_2, …, c_n, with maximum cell displacement M
  - Minimize wirelength and stitch errors
  - An algorithm supports a cost function generalizes wirelength, movement and stitch errors

Movement

$$cost_i(p_i) = \tau \cdot WL(p_i) + \phi \cdot MOV(p_i) + \nu \cdot SP(p_i)$$

Wirelength cost

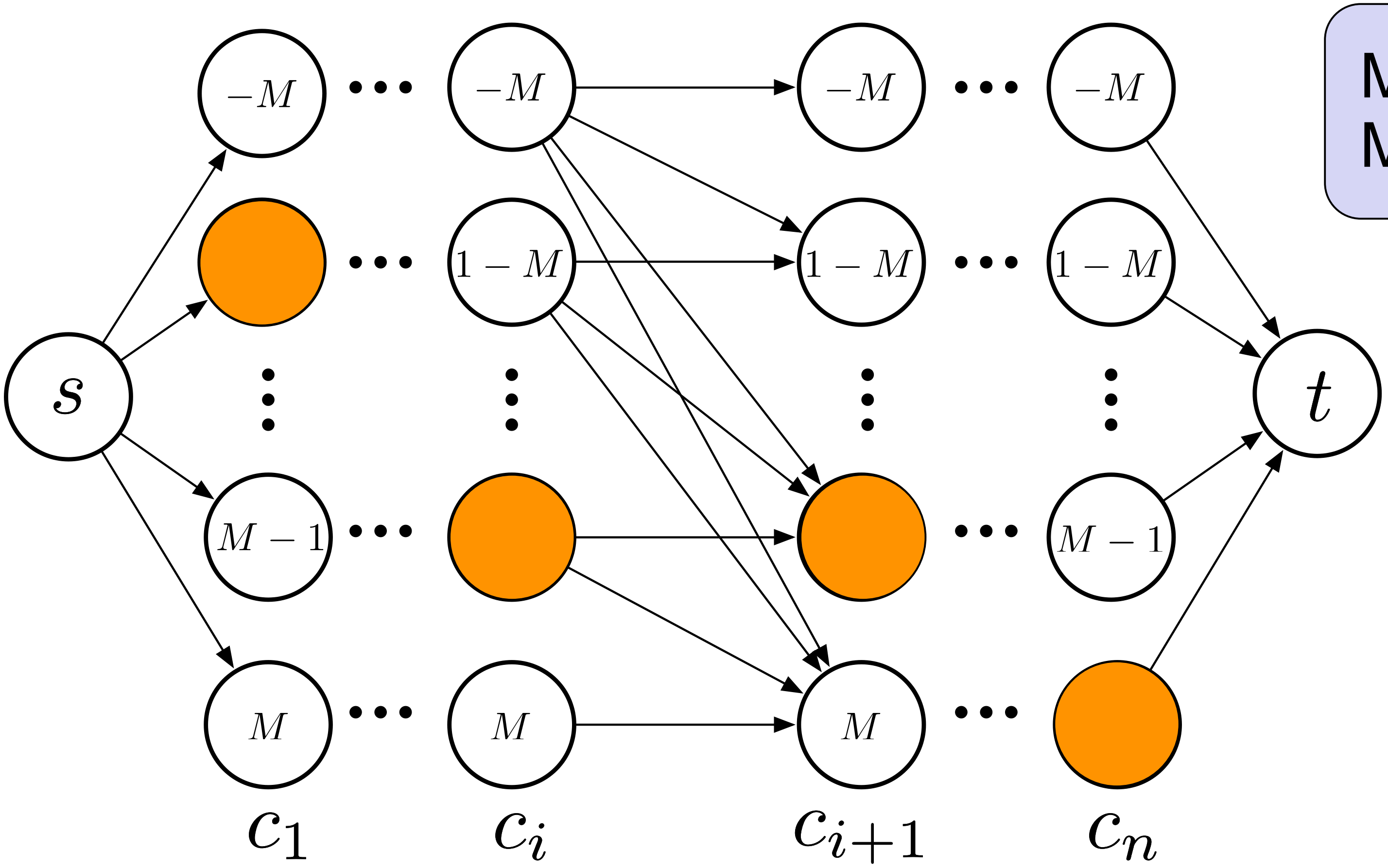
Stitch error penalty

$$SP(p_i) = \begin{cases} 0, & no\ stitch\ error \\ large\ number, & stitch\ error \end{cases}$$

Note: $\tau = 10, \phi = 1, \upsilon = 1$ in the experiment

Single Row Placement

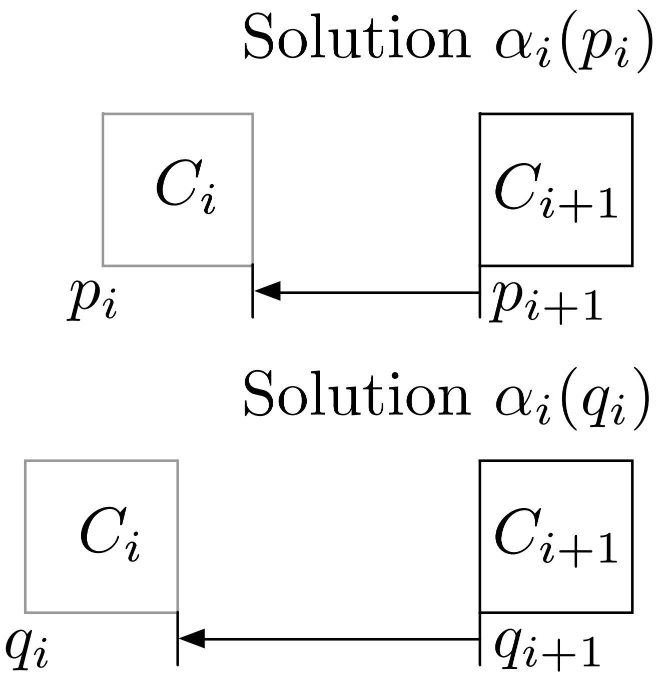
- Given a set of ordered cells c_1, c_2, …, c_n, with maximum cell displacement M
  - Shortest path solved by dynamic programming
  - **O(nM^2)**

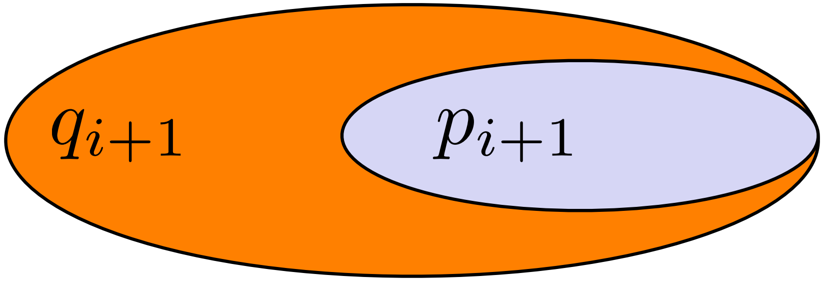


M < 10?
M > 30?

Speedup with Pruning Techniques

- Pruning technique 1
  - Let $t_i(p_i)$ denote the cost of placement solution from c_1 to c_i in which c_i is placed at p_i
  - Comparing two solutions $\alpha_i(p_i)$ and $\alpha_i(q_i)$, if $t_i(p_i) \geq t_i(q_i)$ and $p_i \geq q_i$, then $\alpha_i(p_i)$ is inferior to $\alpha_i(q_i)$.
  - Prune inferior solutions

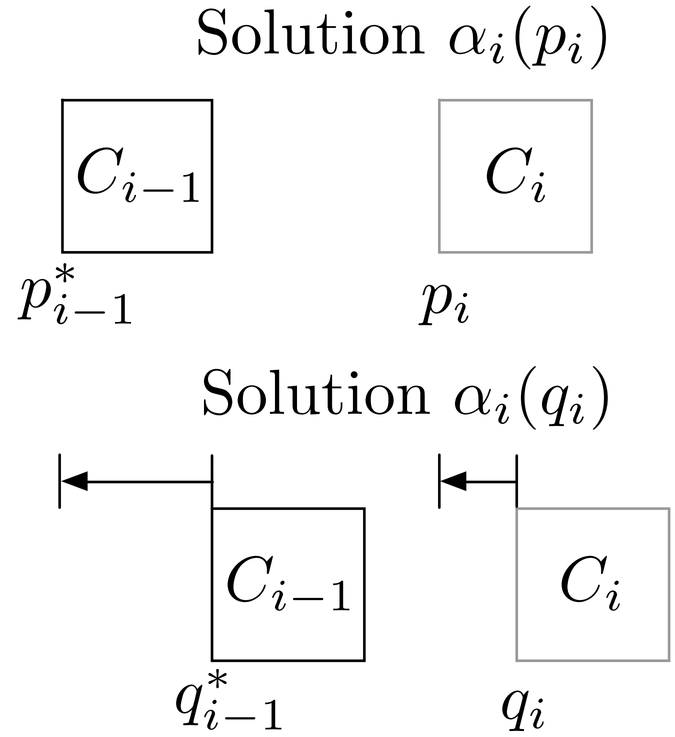


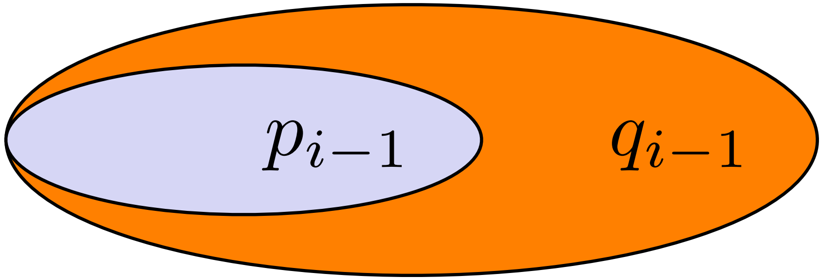


Value sets of p_{i+1} and q_{i+1}

Speedup with Pruning Techniques

- Pruning technique 2
  - Let p_{i-1}^* be the optimal position of cell c_{i-1} when cell c_i is placed at p_i
  - Let q_{i-1}^* be the optimal position of cell c_{i-1} when cell c_i is placed at q_i
  - If $q_i \geq p_i$, then $q_{i-1}^* \geq p_{i-1}^*$
  - Reduce searching ranges

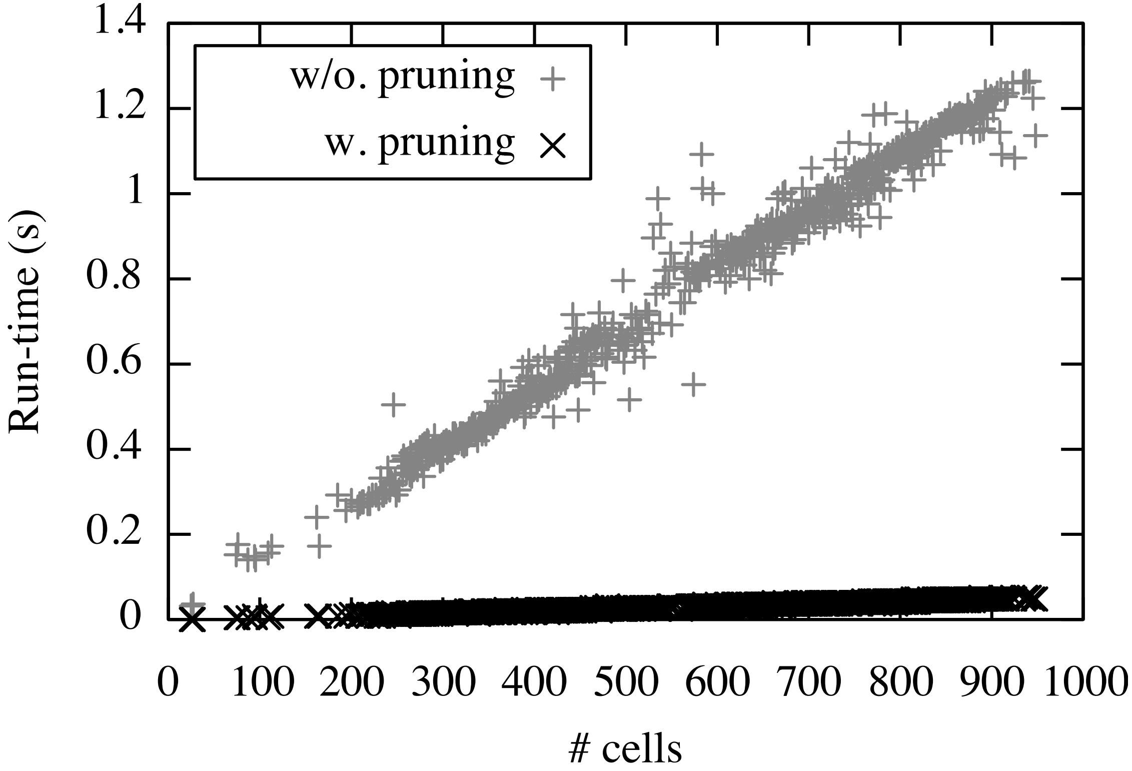




Value sets of p_{i-1} and q_{i-1}

Effectiveness of Speedup Techniques

- O(nM) complexity
  - Requirements: $cost_i(p_i)$ only depends on p_i
  - 30x speedup
  - Keep optimality



Resolve Stitch Errors in Dense Regions

- Global swap to smooth out density
  - $score(c_i, c_j) = \Delta sHPWL - \lambda \cdot P_{ds} - \mu \cdot P_{ov}$

Overlap penalty

sHPWL change

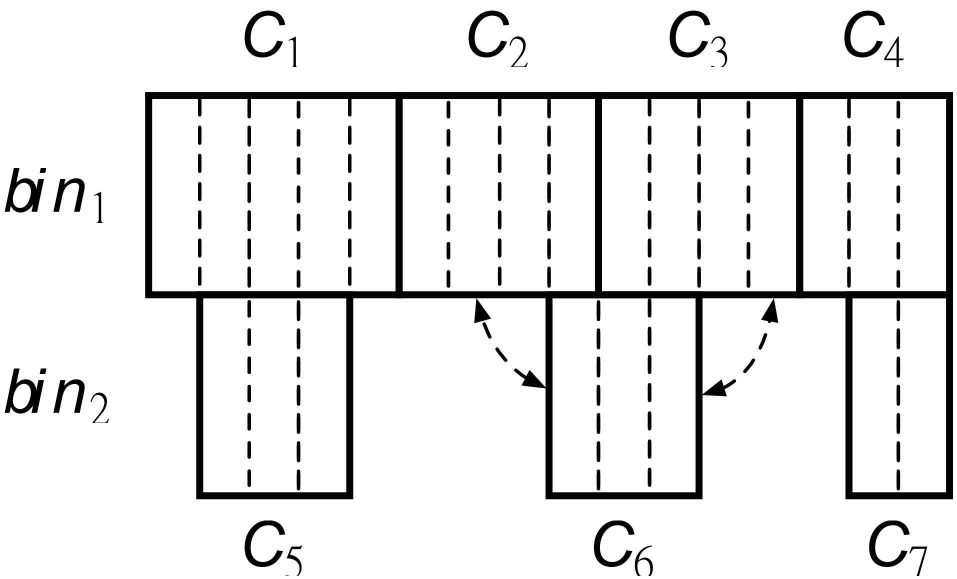
Normalized penalty of dangerous site density

$$P_{ds} = \max(0, |D'_{ds}(i) - D'_{ds}(j)| - |D_{ds}(i) - D_{ds}(j)|) \cdot A_b$$

$D_{ds}(i)$: the density of dangerous sites in bin B_i before swap

$D'_{ds}(i)$: the density of dangerous sites in bin B_i after swap

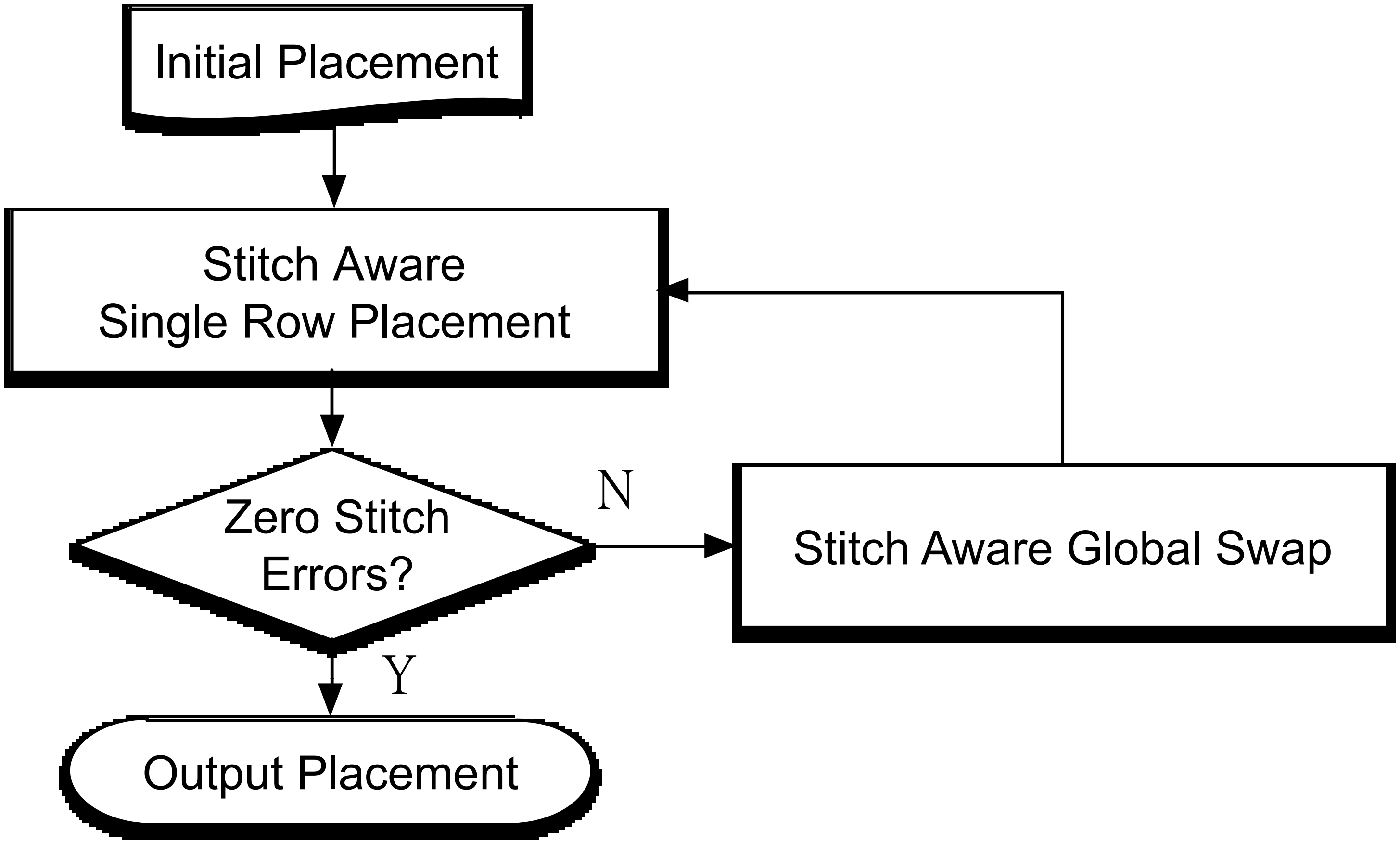
A_b: bin area



Achieve better density of dangerous sites

Note: $sHPWL = HPWL \times (1 + \alpha \times P_{ABU})$ from ICCAD 2013 Contest

Overall Flow



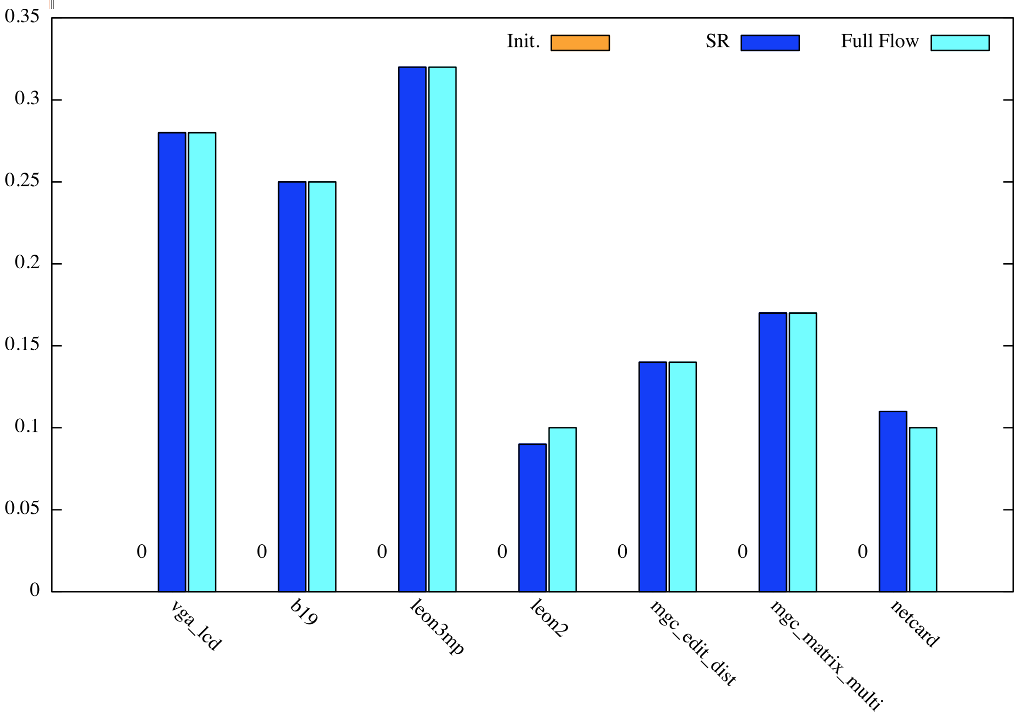
Experimental Environment Setup

- Implemented in C++
- 8-Core 3.4GHz Linux server with 32GB RAM
- ICCAD 2014 contest benchmark
  - Mapped to Nangate 15nm Standard Cell Library
  - Legalized with RippleDP [Chow+,ISPD'14]

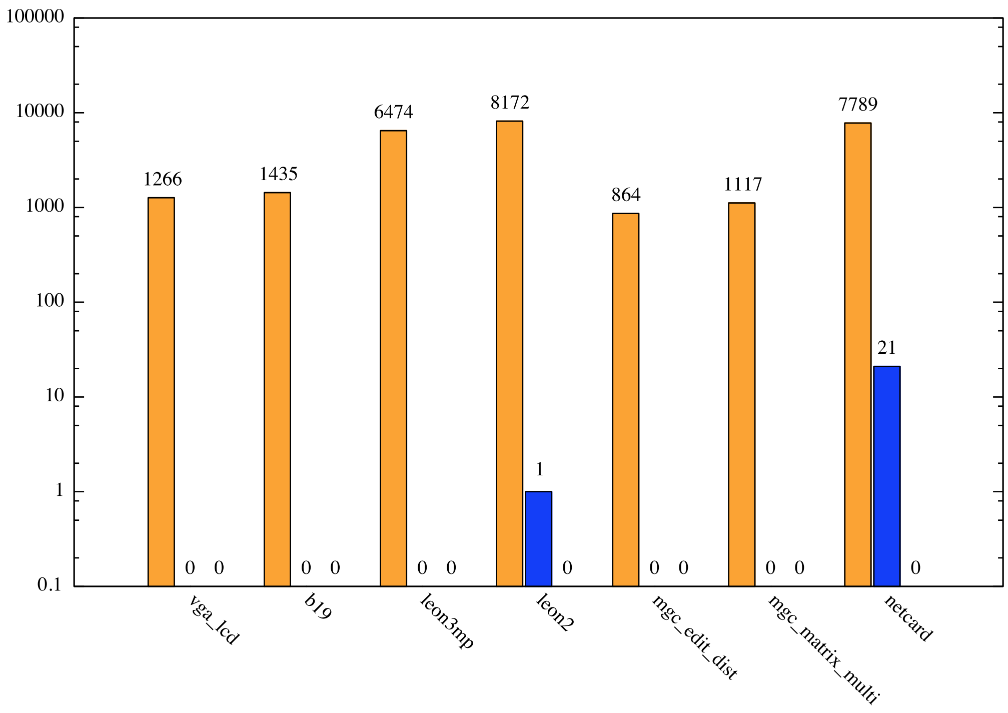
Design	#cells	#nets	#blockages
vga_lcd	165K	165K	0
b19	219K	219K	0
leon3mp	649K	649K	0
leon2	794K	795K	0
mgc_edit_dist	131K	133K	13
mgc_matrix_mult	155K	159K	16
netcard	959K	961K	12

Experimental Results

Wirelength Improvement %



Final Stitch Errors

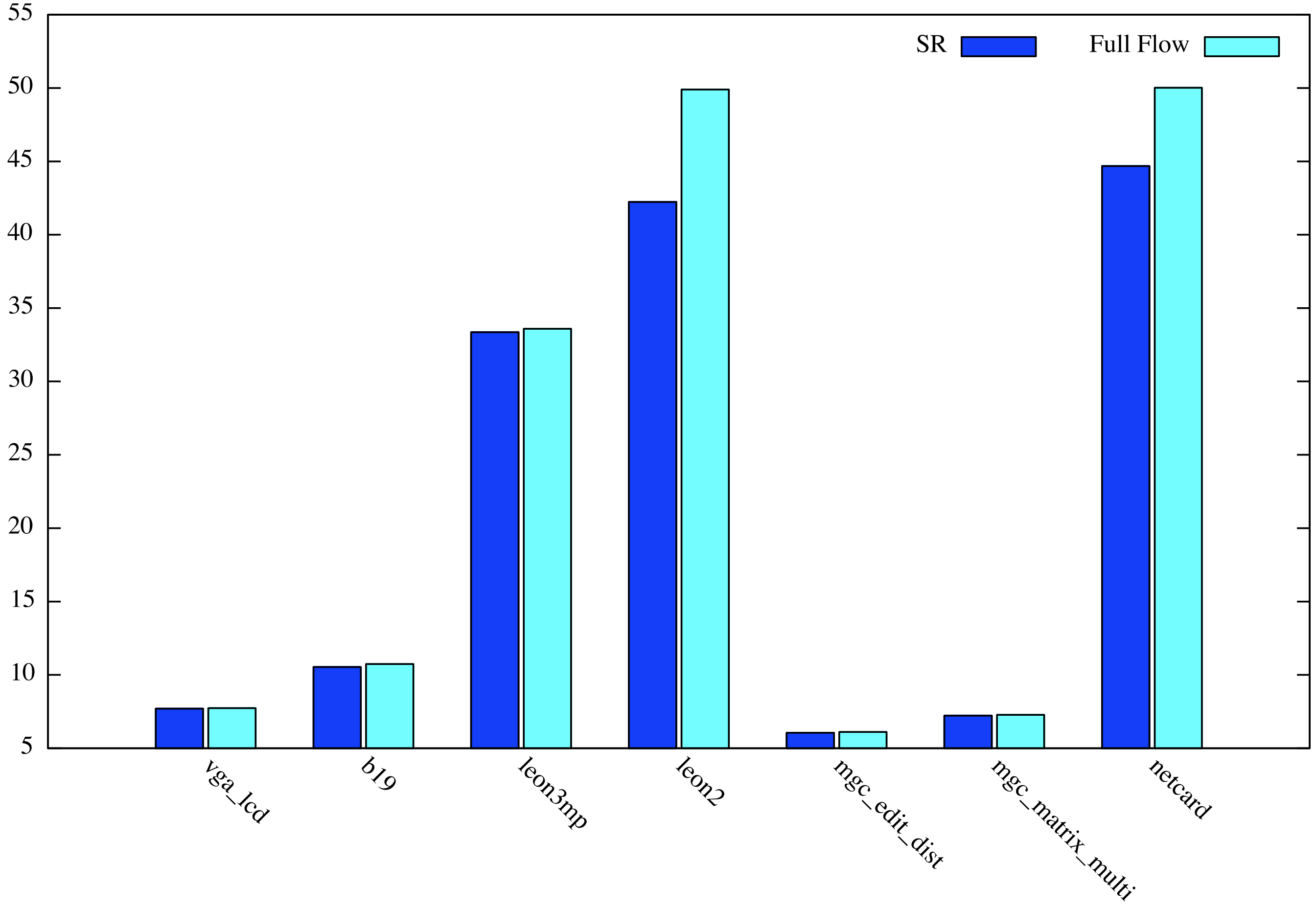


Init.: initial input placement
SR: single row algorithm only
Full Flow: apply full flow including single row algorithm and global swap

Runtime Comparison

- Full flow is slightly slower than SR
  - Only apply to regions still containing stitch errors

Runtime (s)



Conclusion

- Methodology to handle e-beam stitch errors during detailed placement stage
- A linear time single row algorithm with highly-adaptable objective functions
- Better EBL friendliness
- Future work
  - Consider interaction between placement and routing for EBL friendliness

Thanks